# Micropower Dual CMOS Voltage Comparator

The NCV2393 and TS393 are micropower CMOS dual voltage comparators. They feature extremely low consumption of 6  $\mu$ A typical per comparator and operate over a wide temperature range of T<sub>A</sub> = -40 to 125°C. The NCV2393 and TS393 are available in an SOIC-8 package.

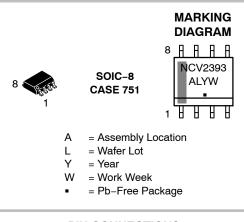
# Features

- Extremely Low Supply Current: 6 µA Typical Per Channel
- Wide Supply Range: 2.7 to 16 V
- Extremely Low Input Bias Current: 1 pA Typical
- Extremely Low Input Offset Current: 1 pA Typical
- Input Common Mode Range Includes V<sub>SS</sub>
- High Input Impedance:  $10^{12} \Omega$
- Pin-to-Pin Compatibility with Dual Bipolar LM393
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

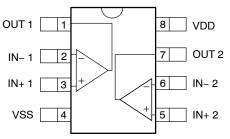


# **ON Semiconductor®**

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# PIN CONNECTIONS



### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NCV2393DR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel
TS393DR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel

+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## **PIN DESCRIPTION**

Pin	Name	Туре	Description
1	OUT 1	Output	Output of comparator 1. The open-drain output requires an external pull-up resistor.
2	IN- 1	Input	Inverting input of comparator 1
3	IN+ 1	Input	Non-inverting input of comparator 1
4	VSS	Power	Negative supply
5	IN+ 2	Input	Non-inverting input of comparator 2
6	IN- 2	Input	Inverting input of comparator 2
7	OUT 2	Output	Output of comparator 2. The open-drain output requires an external pull-up resistor.
8	VDD	Power	Positive supply

### ABSOLUTE MAXIMUM RATINGS (Note 1)

Over operating free-air temperature, unless otherwise stated

Parameter	Limit	Unit
Supply Voltage, V <sub>S</sub> (V <sub>DD</sub> -V <sub>SS</sub> )	18	V
INPUT AND OUTPUT PINS		
Input Voltage (Note 2)	18	V
Input Differential Voltage, V <sub>ID</sub> (Note 3)	±18	V
Input Current (through ESD protection diodes)	50	mA
Output Voltage	18	V
Output Current	20	mA
TEMPERATURE		
Storage Temperature	-65 to +150	°C
Junction Temperature	150	°C
ESD RATINGS		
Human Body Model	1500	V
Machine Model	50	V

#### LATCH-UP RATINGS

Latch-up Current	100	mA
Stresses exceeding those listed in the Maximum Batings table may damage the device. If any of these	limits are exceeded, device fu	nctionality

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Stresses beyond the absolute maximum ratings can lead to reduced reliability and damage.

 Excursions of input voltages may exceed the power supply level. As long as the common mode voltage [V<sub>CM</sub> = (V<sub>IN</sub>+ + V<sub>IN</sub>-)/2] remains within the specified range, the comparator will provide a stable output state. However, the maximum current through the ESD diodes of the input stage must strictly be observed.

3. Input differential voltage is the non-inverting input terminal with respect to the inverting input terminal. To prevent damage to the gates, each comparator includes back-to-back zener didoes between input terminals. When differential voltage exceeds 6.2 V, the diodes turn on. Input resistors of 1 kΩ have been integrated to limit the current in this event.

4. This device series incorporates ESD protection and is tested by the following methods: ESD Human Body Model tested per AEC-Q100-002 (JEDEC standard: JESD22-A114) ESD Machine Model tested per AEC-Q100-003 (JEDEC standard: JESD22-A115) Latch-up Current tested per JEDEC standard: JESD78.

### THERMAL INFORMATION (Note 5)

Thermal Metric	Symbol	Value	Unit
Junction-to-Ambient (Note 6)	$\theta_{JA}$	190	°C/W
Junction-to-Case Top	$\Psi_{JT}$	107	°C/W

5. Short-circuits can cause excessive heating and destructive dissipation. Values are typical.

6. Multilayer board, 1 oz. copper, 400 mm<sup>2</sup> copper area, both junctions heated equally

## **OPERATING CONDITIONS**

Parameter	Symbol	Limit	Unit
Supply Voltage (V <sub>DD</sub> – V <sub>SS</sub> )	V <sub>S</sub>	+2.7 to +16	V
Operating Free Air Temperature Range	T <sub>A</sub>	-40 to +125	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

ELECTRICAL CHARACTERISTICS:  $V_S = +3 V$ (Boldface limits apply over the specified temperature range,  $T_A = -40^{\circ}C$  to  $+125^{\circ}C$ , guaranteed by characterization and/or design.)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	V <sub>OS</sub>	$V_{CM} = mid-supply$		1.4	13	mV
					14	mV
Input Bias Current (Note 7)	I <sub>IB</sub>	V <sub>CM</sub> = mid-supply		1		pА
					600	pА
Input Offset Current (Note 7)	I <sub>OS</sub>	V <sub>CM</sub> = mid-supply		1		pА
					300	pА
Input Common Mode Range	V <sub>CM</sub>		V <sub>SS</sub>	/ <sub>SS</sub>	V <sub>DD</sub> – 1.5	V
			V <sub>SS</sub>		V <sub>DD</sub> - 2	v
Common Mode Rejection Ratio	CMRR	$V_{CM}$ = $V_{SS}$ to $V_{CM}$ = $V_{DD}$ – 1.5 V		70		dB

## **OUTPUT CHARACTERISTICS**

Output Voltage Low	V <sub>OL</sub>	$V_{ID} = -1 V$ , $I_{OL} = +6 mA$	V <sub>SS</sub> + 300	V <sub>SS</sub> + 450	mV
				V <sub>SS</sub> + 700	mV
Output Current High	I <sub>OH</sub>	V <sub>ID</sub> = +1 V, V <sub>OH</sub> = +3 V	2	40	nA
				1000	nA

## DYNAMIC PERFORMANCE

Propagation Delay Low to High	t <sub>PLH</sub>	$V_{CM}$ = mid–supply, f = 10 kHz, R <sub>PU</sub> = 5.1 k $\Omega$ ,	5 mV overdrive	2.1	μs
riigii		$C_{L} = 50 \text{ pF}$	TTL input	0.6	μs
Propagation Delay High to Low	t <sub>PHL</sub>	$V_{CM}$ = mid–supply, f = 10 kHz, R <sub>PU</sub> = 5.1 kΩ,	5 mV overdrive	3.9	μs
Low		$C_{L} = 50 \text{ pF}$	TTL input	0.2	μs

#### POWER SUPPLY

Power Supply Rejection Ratio	PSRR	$V_{S} = +3 \text{ V to } +5 \text{ V}$	70		dB
Quiescent Current	I <sub>DD</sub>	Per channel, no load, output = LOW	6	15	μΑ
				20	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

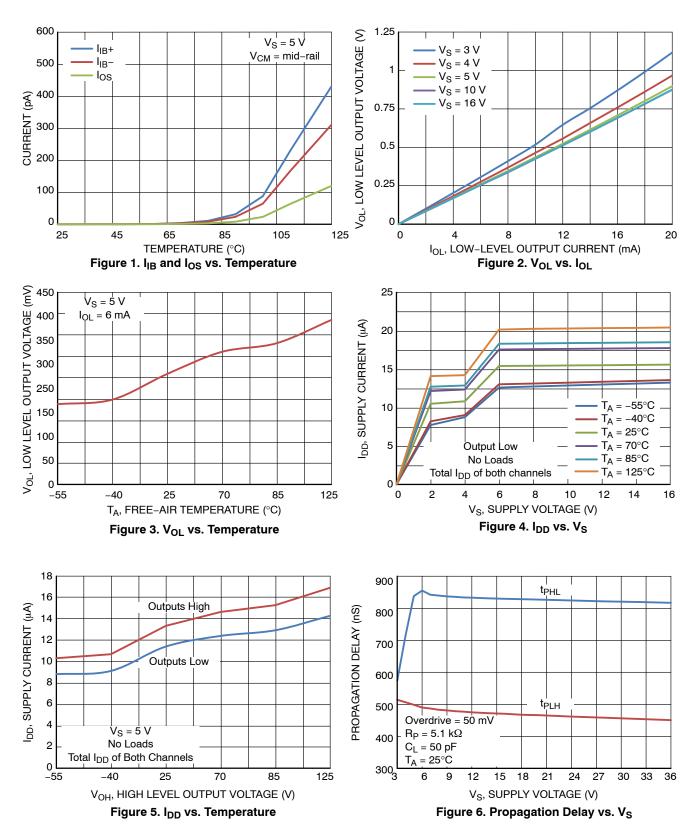
7. Guaranteed by characterization and/or design.

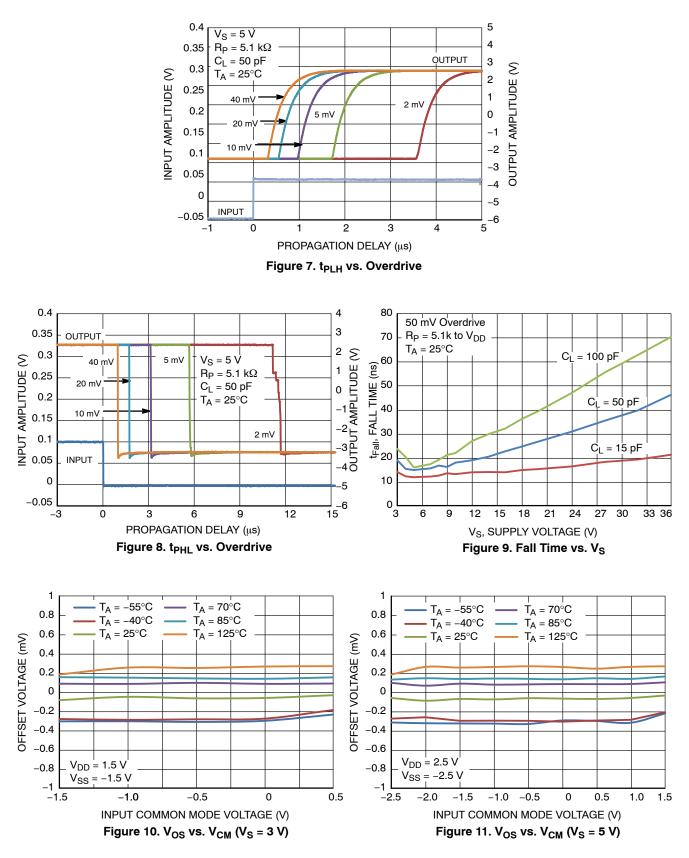
**ELECTRICAL CHARACTERISTICS:**  $V_S = +5 V$ , unless otherwise noted (**Boldface** limits apply over the specified temperature range,  $T_A = -40$ °C to +125°C, guaranteed by characterization and/or design.)

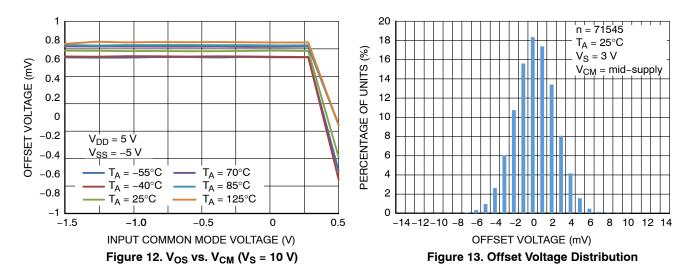
Parameter	Symbol	Conditio	ns	Min	Тур	Max	Unit
INPUT CHARACTERISTICS	\$	1					
Offset Voltage	V <sub>OS</sub>	V <sub>CM</sub> = mid–supply V, V	V <sub>S</sub> = 5 V to 10 V	T	1.4	13	mV
						14	mV
Input Bias Current	I <sub>IB</sub>	V <sub>CM</sub> = mid-s	supply		1		pА
(Note 8)						600	pА
Input Offset Current	I <sub>OS</sub>	V <sub>CM</sub> = mid-s	supply		1		pА
(Note 8)						300	pА
Input Common Mode Range	V <sub>CM</sub>			V <sub>SS</sub>		V <sub>DD</sub> – 1.5	V
				V <sub>SS</sub>		V <sub>DD</sub> - 2	v
Common Mode Rejection Ratio	CMRR	$V_{CM}$ = $V_{SS}$ to $V_{CM}$ = $V_{DD}$ – 1.5 V			71		dB
OUTPUT CHARACTERISTI	CS						-
Output Voltage Low	V <sub>OL</sub>	V <sub>ID</sub> = -1 V, I <sub>OL</sub> = +6 mA			V <sub>SS</sub> + 260	V <sub>SS</sub> + 350	mV
						V <sub>SS</sub> + 550	mV
Output Current High	I <sub>OH</sub>	V <sub>ID</sub> = +1 V, V <sub>O</sub>	<sub>H</sub> = +5 V		2	40	nA
						1000	nA
DYNAMIC PERFORMANCE							
Fall Time	t <sub>FALL</sub>	50 mV overdrive, f = 10 k $C_L = 50$			25		ns
Propagation Delay Low to	t <sub>PLH</sub>	$V_{CM} = mid-supply,$	5 mV overdrive		2.1		μs
High		f = 10 kHz, R <sub>PU</sub> = 5.1 kΩ, C <sub>L</sub> = 50 pF	10 mV overdrive	VSS VD 1   VSS VD 1   VSS VD 2   71 V   71 V   260 VS 33   VSS VS 33   260 VS 35   2 4   10 10   25 25		μs	
			20 mV overdrive		0.8		μs
			40 mV overdrive		0.5		μs
			TTL input		0.6		μs
Propagation Delay High to Low	t <sub>PHL</sub>	$V_{CM}$ = mid–supply, f = 10 kHz, R <sub>PU</sub> = 5.1 k $\Omega$ ,	5 mV overdrive		5.8		μs
		$C_{L} = 50 \text{ pF}$	10 mV overdrive		3.2		μs
			20 mV overdrive		1.7		μs
			40 mV overdrive		1.0		μs
			TTL input		0.3		μs
POWER SUPPLY							
Power Supply Rejection	PSRR	VS = +5 V to :	= +10 V		80		dB

Power Supply Rejection Ratio	PSRR	VS = +5 V to = +10 V	80		dB
Quiescent Current	I <sub>DD</sub>	Per channel, no load, output = LOW	6	15	μΑ
				20	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 8. Guaranteed by characterization and/or design











\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# STYLES ON PAGE 2

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STYLE 1: PIN 1. EMITTER COLLECTOR 2. COLLECTOR 3. 4. EMITTER EMITTER 5. BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: CATHODE 1 PIN 1. 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT 3. 4. GND 5. IOUT 6. IOUT IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: PIN 1. GROUND BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE P-SOURCE 3 P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE 2. ANODE SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. CATHODE 8. STYLE 22 PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC COMMON CATHODE/VCC 3 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 COMMON ANODE/GND 8. STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4. SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5. 6.

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. 4. DRAIN, #2 GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 DRAIN 1 7. 8. **MIRROR 1** STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. LINE 1 OUT 8. STYLE 27: PIN 1. ILIMIT 2 OVI 0 UVLO З. 4. INPUT+ 5. SOURCE SOURCE 6. SOURCE 7. 8 DRAIN

#### DATE 16 FEB 2011

STYLE 4: ANODE ANODE PIN 1. 2. ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE #2 3. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. 4. GATE 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE 2. EMITTER 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW\_TO\_GND 2. DASIC OFF DASIC\_SW\_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

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SOURCE 1/DRAIN 2

7.

8. GATE 1

7.

8

rights of others

COLLECTOR, #1

COLLECTOR, #1

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